

Amendments of the Claims

The following listing of claims will replace all prior versions, and listings, of claims in the above-identified patent application:

Listing of Claims

1-54. (canceled)

55. (previously presented) A semiconductor comprising:

a substrate having a downwardly extending cavity formed therein;

5 a first spiral conductor formed in the cavity, said first spiral conductor being fabricated substantially in a first horizontal plane within the cavity; and

10 a second spiral conductor formed in the cavity, said second spiral conductor being fabricated substantially in a second horizontal plane within the cavity and above the first plane, wherein the first and second spiral conductors are positioned to be inductively coupled during operation.

56. (previously presented) The semiconductor of claim 55 wherein the first and second spiral conductors have an inductive coupling coefficient greater than about 0.8.

57. (previously presented) The semiconductor of claim 55 wherein:

each of said inductors has a center; and
said centers are substantially aligned along

5 an axis.

58. (previously presented) The semiconductor of claim 57 wherein:

said first inductor has a first number of turns; and

5 said second inductor has a second number of turns.

59. (previously presented) The semiconductor of
claim 58 wherein said first and second numbers are equal.

60. (previously presented) The semiconductor of
claim 59 wherein:

said semiconductor has a major surface
defining a plane; and

5 said cavity is formed in said major surface.

61. (previously presented) The semiconductor of
claim 60 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall substantially perpendicular to
said plane.

62. (previously presented) The semiconductor of
claim 60 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall at an oblique angle relative to
said plane.

63. (previously presented) The semiconductor of
claim 62 wherein said side wall is at an angle of about
54.74° relative to said plane.

64. (previously presented) The semiconductor of
claim 58 wherein:

said semiconductor has a major surface
defining a plane; and

5 said cavity is formed in said major surface.

65. (previously presented) The semiconductor of
claim 64 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall substantially perpendicular to
said plane.

66. (previously presented) The semiconductor of
claim 64 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall at an oblique angle relative to
said plane.

67. (previously presented) The semiconductor of
claim 66 wherein said side wall is at an angle of about
54.74° relative to said plane.

68. (previously presented) The semiconductor of
claim 57 wherein:

said semiconductor has a major surface
defining a plane; and

5 said cavity is formed in said major surface.

69. (previously presented) The semiconductor of
claim 68 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall substantially perpendicular to
said plane.

70. (previously presented) The semiconductor of
claim 68 wherein said cavity comprises:

a bottom surface substantially parallel to
said plane; and

5 a side wall at an oblique angle relative to
said plane.

71. (previously presented) The semiconductor of
claim 70 wherein said side wall is at an angle of about
54.74° relative to said plane.

72-78. (canceled)